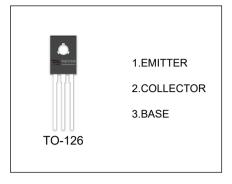


BD034 TRANSISTOR (PNP)

FEATURES

- High Transition Frequency
- High Collector Current



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BD034	TO-126	Bulk	200pcs/Bag
BD034-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-110	V
V _{CEO}	Collector-Emitter Voltage	-95	V
V _{EBO}	Emitter-Base Voltage	-7	V
Ic	Collector Current	-2.5	Α
Pc	Collector Power Dissipation	1.25	W
R _{0JA}	Thermal Resistance From Junction To Ambient	100	°C/W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}$



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA,I _E =0	-110			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA,I _B =0	-95			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA,I _C =0	-7			V
Collector cut-off current	I _{CBO}	V _{CB} =-100V,I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V,I _C =0			-1	μA
DC current gain	h _{FE(1)}	V _{CE} =-2V, I _C =-100mA	100		560	
	h _{FE(2)}	V _{CE} =-2V, I _C =-1.5A	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A,I _B =-200mA			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V, I _C =-500mA			-1	V
Transition frequency	f⊤	V _{CE} =-1V,I _C =-250mA, f=1MHz	3			MHz

CLASSIFICATION OF $h_{\text{FE}(1)}$

RANK	R	S	Т	U
RANGE	100-200	140-280	200-400	280-560